This index replaces the one originally published in the December 1994 issue of this TRANSACTIONS. Due to a programming error, the names of several authors were omitted from their article citations. This new version corrects the errors of omission and includes author entries not found in the original. We regret any inconvenience.

RENUKA P. JINDAL
Editor

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This index covers all technical items — papers, correspondence, reviews, etc. — that appeared in this periodical during 1994, and items from previous years that were commented upon or corrected in 1994.

The Author Index contains the primary entry for each item, listed under the first author's name, and cross-references from all coauthors. The Subject Index contains several entries for each item under appropriate subject headings, and subject cross-references.

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Feedback lasers; cf. Distributed-feedback lasers

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FET integrated circuits; cf. CMOS integrated circuits; FETs; MOS integrated circuits

FET integrated circuits, analog; cf. CMOS integrated circuits, analog

FET integrated circuits, memory; cf. CMOS integrated circuits, memory; MOS integrated circuits, memory

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Semiconductor noise; cf. Semiconductor device noise

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Semiconductor-on-insulator; cf. Silicon-on-insulator

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